IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Li

Attorney Docket: 2003 P 54557 US

Filed:

Herewith

Examiner:

TBD

Serial No.:

TBD

Art Unit:

TBD

For:

Transistor with Doped Gate Dielectric

Mail Stop: Patent Application Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

The Applicant wishes to bring to the attention of the Patent and Trademark Office the information noted on the enclosed form PTO/SB/08A that may be considered material to the examination of the above-identified application.

No fee is due at this time, as this Information Disclosure Statement is being filed concurrently with the patent application.

Respectfully submitted,

February 3, 2004

Date

Kay Houston

Attorney for Applicant

Reg. No. 38,495

Slater & Matsil, L.L.P. 17950 Preston Rd., Suite 1000 Dallas, TX 75252 (972) 732-1001 (phone) (972) 732-9218 (fax)

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| STATEMENT BY APPLICANT | | | LICANT | First Named Inventor | Li | |
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| (use as many sheets as necessary) | | | cessary) | Examiner Name | TBD | |
| Sheet | 1 | of | | Attorney Docket Number | 2003 P 54557 US | |

| U.S. PATENT DOCUMENTS | | | | | | |
|-----------------------|--------------|--------------------------------------------|------------------|-----------------------------------------|---------------------------------------------------------------|--|
| Examiner Initials* | Cita | Document Number | Publication Date | Name of Patentee or | Pages, Columns, Lines, Where Relevant Passages or Relevant | |
| | Cite No.1 | Number - Kind Code ^{2 (if known)} | MM-DD-YYYY | Applicant of Cited Document | Relevant Passages or Relevant Figures Appear | |
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| OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS | | | | |
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| Examiner Initials* | Cite ₁ No. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T ² | |
| | 1 | INUMIYA, S., et al., "Fabrication of HfSiON Gate Dielectrics by Plasma Oxidation and Nitridation, Optimized for 65nm node Low Power CMOS Applications," 2003 Symposium on VLSI Technology Digest of Technical Papers, pp. 18–19, Document No. 4-89114-035-6/03. | | |
| | 2 | WOLF, S., "Silicon Processing for the VLSI Era: Diffusion in Silicon" pp. 336–339. | | |

| Examiner | Date | |
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